Green Journals

International Approved Journals

Journal Information

Journal Title	SEMICONDUCTOR SCIENCE AND TECHNOLOGY
Publisher	IOP PUBLISHING LTD
ISSN	0268-1242
E-ISSN	1361-6641
Database	Clarivate
Domain	Physical Sciences

Classification History

Year	A+	A	B	C
2026		✓	✓	
2025		✓	✓	
2024		✓	✓	
2023		✓	✓	
2021/2022		✓	✓	
2020		✓	✓	
2019		✓	✓	
2018		✓		

Classification: The table above shows all journal classifications recorded for each classification year in the Green Journals database. A journal may have more than one classification in the same year.

Recent Articles

High-Performance GaN HEMTs on an Ultrathin 4H-SiC/Diamond Engineered Substrate via Optimized Epitaxial Growth
2026-11-2
Authors: Yipei Lei, Xinhua Wang, Fengwen Mu et al.
DOI: 10.1088/1361-6641/aebca9

Two-wavelength micro-Raman spectroscopy and atomistic modeling of n-InSb:Te single crystals: orientation dependence of phonon scattering and the influence of carrier concentration
2026-10-29
Authors: Aleksandr Maksimov, Yuri Tarasov, Nikita Sanzharovskii et al.
DOI: 10.1088/1361-6641/aebb5d

Novel Projected-Pitch Technology and Non-Planar Surface LDMOS with Ultra-Low Specific On-Resistance
2026-10-29
Authors: Hanwen Bai, Dingxiang Ma, Jiawei Wang et al.
DOI: 10.1088/1361-6641/aebb5e

Effect of Intrinsic Layer Thickness on the Power Conversion Efficiency of GaN p-i-n Betavoltaic Cells
2026-10-27
Authors: Huiyun Jung, Jae-Won Park, Dong-Seok Kim et al.
DOI: 10.1088/1361-6641/aeba0f

Design Optimization of Strain Distribution and Polarization-Induced 2DEG Formation in III-Nitride/GaN Heterostructures
2026-10-27
Authors: Priyesh Kumar, Nirjara Anubhav Mehta, Jhuma Saha
DOI: 10.1088/1361-6641/aeba0d

Low-Loss Superjunction SiC MOSFET with Improved Breakdown Voltage and Reverse-Recovery Performance
2026-10-27
Authors: Xiangqi Hong, Xun Li
DOI: 10.1088/1361-6641/aeba0c

Negative-Capacitance Germanium-on-AlAs Nanosheet FETs for Ultra-Low-Power Logic Applications
2026-10-26
Authors: Anshu Pathak, Shawn Lewis, Chaitrali Samant et al.
DOI: 10.1088/1361-6641/aeb96f

A High-Performance Depletion Mode Graded AlGaN/GaN HEMT with Trilayer Cap and AlInGaN Back Barrier for Analog and RF Applications
2026-10-26
Authors: Amit Agarwal, Sumit Kale
DOI: 10.1088/1361-6641/aeb970

Electrothermal Parameter Identification from DC I-V Data for Compact Drain-Current Models of Gan-On-SiC RF HEMTS: A Comparative Metaheuristic Study
2026-10-26
Authors: Syed Mostafa Shihab Uddin, Famin Rahman Rakib, Anwar Jarndal et al.
DOI: 10.1088/1361-6641/aeb96e

From Growth to Integration: MOCVD epitaxy of h-BN and Heterogeneous Integration
2026-10-23
Authors: Yanchao Wang, Jingnan Dong, Yiwei Duo et al.
DOI: 10.1088/1361-6641/aeb8b5